

Silicon Standard Recovery Diode

$V_{RRM} = 600\text{ V} - 1600\text{ V}$

$I_F = 200\text{ A}$

Features

- High Surge Capability
- Types up to 1600 V V_{RRM}

Three Tower Package



Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	MSRT20060(A)	MSRT20080(A)	MSRT200100(A)	Unit
Repetitive peak reverse voltage	V_{RRM}		600	800	1000	V
RMS reverse voltage	V_{RMS}					V
DC blocking voltage	V_{DC}					V
Continuous forward current	I_F					A
Operating temperature	T_j					$^\circ\text{C}$
Storage temperature	T_{stg}					$^\circ\text{C}$

Parameter	Symbol	MSRT20080(A)	Unit
Diode forward voltage			μA mA

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}	0.	$^\circ\text{C/W}$
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